PMZB370UNE



Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- Low threshold voltage

- Ultra thin package profile with 0.37 mm height
- ESD protection up to 2 kV

1.3 Applications

- Relay driver
- High-speed line driver

- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-	900	mA
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 500 \text{ mA}; T_j = 25 \text{ °C}$		-	370	490	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		2
2	S	source	1	D
3	D	drain	Transparent top view SOT883B (DFN1006B-3)	017aaa255

3. Ordering information

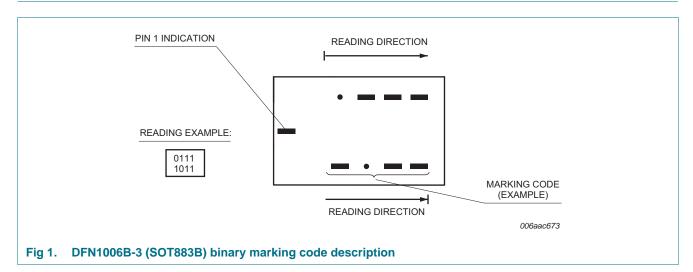
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZB370UNE	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking

Table 4. Marking codes

Type number	Marking code
PMZB370UNE	0000 1000



5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
					V
	1, - 25 0				
gate-source voltage			-8	8	V
drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	900	mΑ
	V _{GS} = 4.5 V; T _{amb} = 100 °C	<u>[1]</u>	-	560	mA
peak drain current	$T_{amb} = 25 ^{\circ}C$; single pulse; $t_p \le 10 \mu s$		-	3.6	Α
total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
		[1]	-	715	mW
	T _{sp} = 25 °C		-	2700	mW
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
diode					
source current	T _{amb} = 25 °C	<u>[1]</u>	-	680	mA
n rating					
electrostatic discharge voltage	НВМ	[3]	-	2000	V
	peak drain current total power dissipation junction temperature ambient temperature storage temperature diode source current n rating	$ \begin{array}{lll} drain\text{-source voltage} & T_j = 25 \ ^{\circ}\text{C} \\ gate\text{-source voltage} \\ drain current & V_{GS} = 4.5 \ ^{\circ}\text{C}, \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \hline V_{GS} = 4.5 \ ^{\circ}\text{C}, \ T_{amb} = 100 \ ^{\circ}\text{C} \\ \hline Peak drain current & T_{amb} = 25 \ ^{\circ}\text{C}; \ single pulse; \ t_p \leq 10 \ \mu s \\ \hline total power dissipation & T_{amb} = 25 \ ^{\circ}\text{C} \\ \hline T_{sp} = 25 \ ^{\circ}\text{C} \\ \hline junction temperature \\ ambient temperature \\ storage temperature \\ \hline diode \\ source current & T_{amb} = 25 \ ^{\circ}\text{C} \\ \hline n \ rating \\ \end{array} $		$ \begin{array}{c} drain\text{-source voltage} \\ gate\text{-source voltage} \\ drain current \\ \hline \\ V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ V_{GS} = 4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C} \\ \hline \\ V_{GS} = 4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C} \\ \hline \\ 11 \\ \hline$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

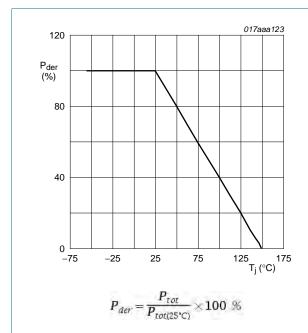
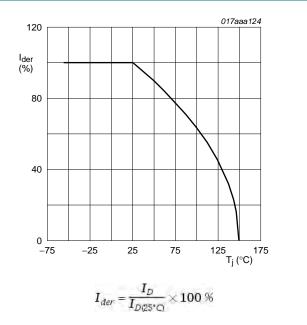


Fig 2. Normalized total power dissipation as a function of junction temperature



g 3. Normalized continuous drain current as a function of junction temperature

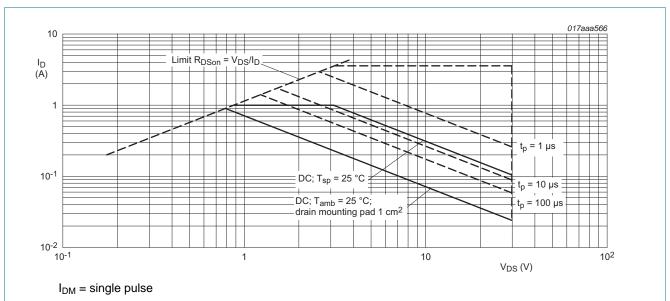


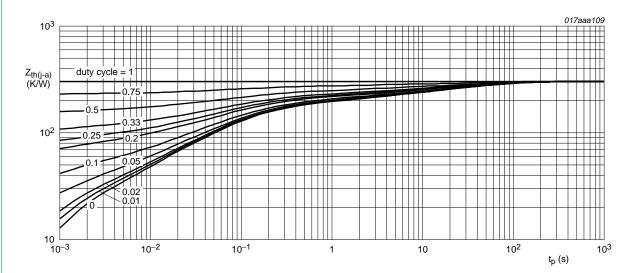
Fig 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

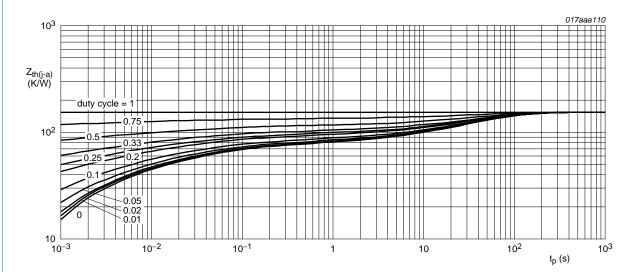
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	305	360	K/W
	from junction to ambient		[2]	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	0.77	1.05	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	3	μΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	3	μΑ
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	0.5	μΑ
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	0.5	μΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 500 \text{ mA}; T_j = 25 \text{ °C}$	-	370	490	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 500 \text{ mA}; T_j = 150 \text{ °C}$	-	650	860	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 400 \text{ mA}; T_j = 25 \text{ °C}$	-	470	750	mΩ
		$V_{GS} = 1.8 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$	-	630	1300	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	1580	-	mS
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 500 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.77	1.16	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.15	-	nC
Q_{GD}	gate-drain charge		-	0.16	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	52	78	pF
C _{oss}	output capacitance	T _j = 25 °C	-	9	-	pF
C _{rss}	reverse transfer capacitance		-	3	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 250 \Omega; V_{GS} = 4.5 \text{ V};$	-	11	22	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	9	-	ns
t _{d(off)}	turn-off delay time		-	54	108	ns
t _f	fall time		-	27	-	ns
Source-di	rain diode					
V _{SD}	source-drain voltage	$I_S = 300 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	0.48	0.76	1.2	V

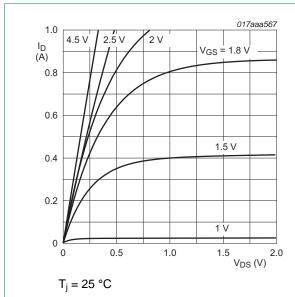


Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values

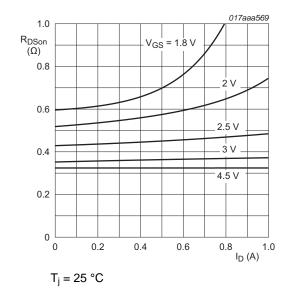


Fig 9. Drain-source on-state resistance as a function of drain current; typical values

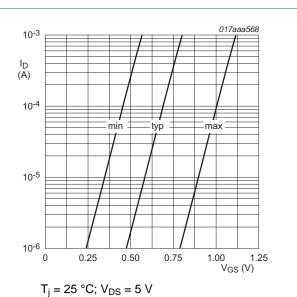


Fig 8. Sub-threshold drain current as a function of gate-source voltage

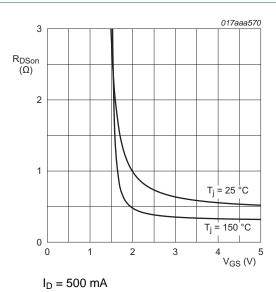


Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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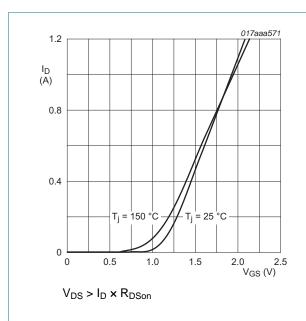


Fig 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

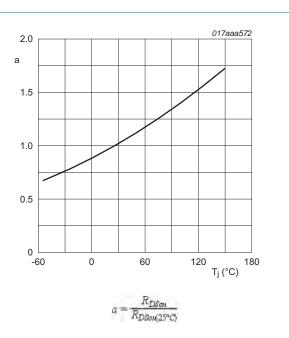


Fig 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

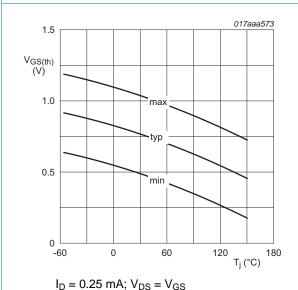


Fig 13. Gate-source threshold voltage as a function of junction temperature

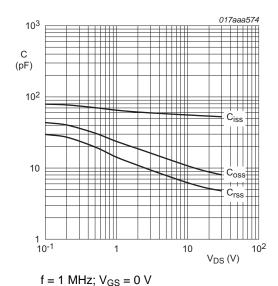
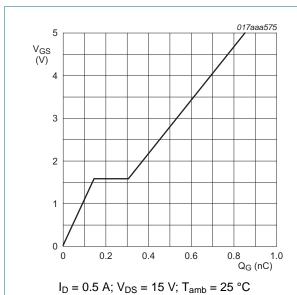


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

values



V_{GS}(pl)

V_{GS}(th)

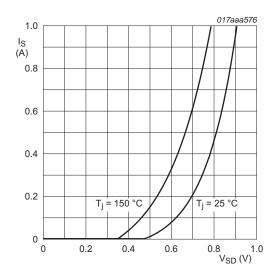
V_{GS}

Q_{GS1}
Q_{GS2}
Q_G(tot)

017aaa137

Fig 15. Gate-source voltage as a function of gate charge; typical values

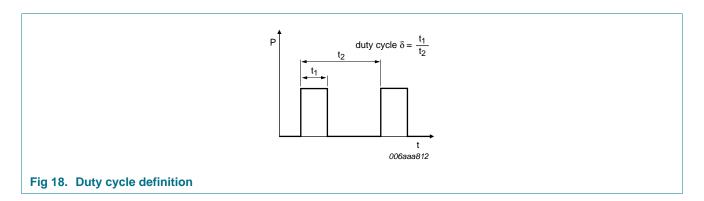
Fig 16. Gate charge waveform definitions



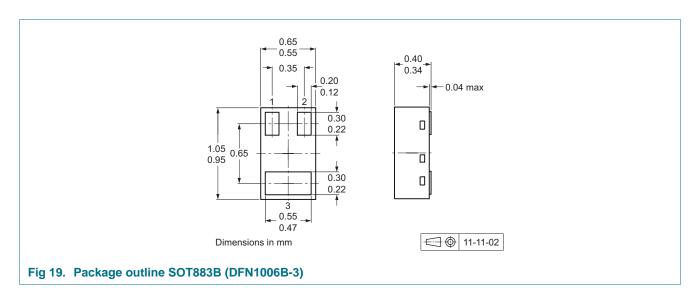
 $V_{GS} = 0 V$

Fig 17. Source current as a function of source-drain voltage; typical values

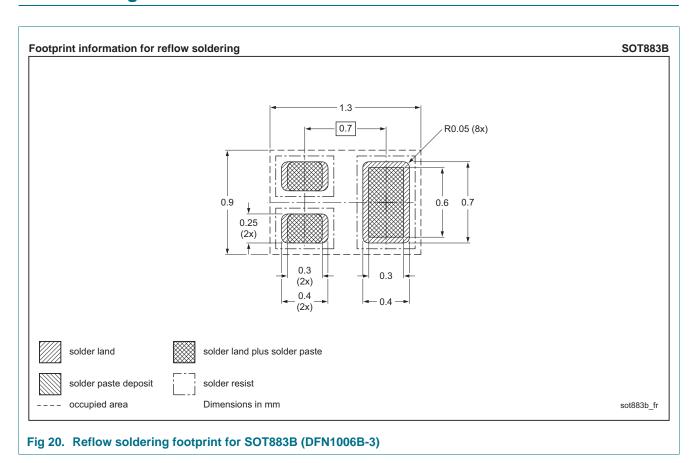
8. Test information



9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMZB370UNE v.1	20120508	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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30 V, single N-channel Trench MOSFET

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30 V, single N-channel Trench MOSFET

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